

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

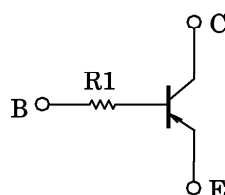
RN2210, RN2211

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT AND DRIVER
CIRCUIT APPLICATIONS

Unit in mm

- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1210, RN1211

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

JEDEC	—
EIAJ	—
TOSHIBA	2-4E1A

Weight : 0.13g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -50V, I _E = 0	—	—	-100	nA
Emitter Cut-off Current	I _{EB0}	V _{EB} = -5V, I _C = 0	—	—	-100	nA
DC Current Gain	h _{FE}	V _{CE} = -5V, I _C = -1mA	120	—	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V
Transition Frequency	f _T	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF
Input Resistor	RN2210	R1	3.29	4.7	6.11	kΩ
	RN2211		7	10	13	

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